

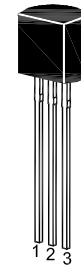
2SC3198

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



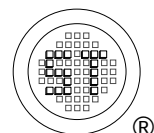
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

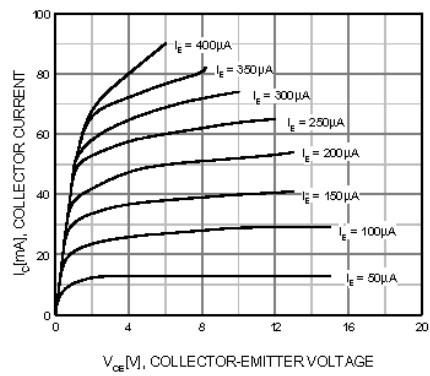
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	50	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

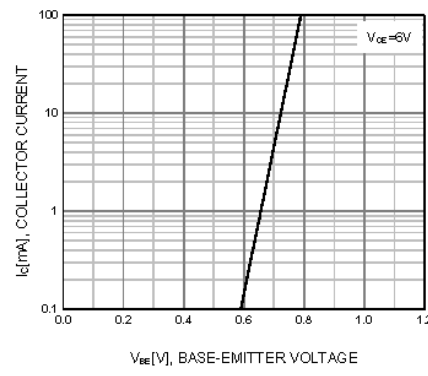
Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 2\text{ mA}$ at $V_{CE} = 6\text{ V}$, $I_C = 150\text{ mA}$ Current Gain Group O Y G L	h_{FE}	70	140	-
	h_{FE}	120	240	-
	h_{FE}	200	400	-
	h_{FE}	350	700	-
	h_{FE}	25	-	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.25	V
Base Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{BE(sat)}$	-	1	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	f_T	80	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	3.5	pF

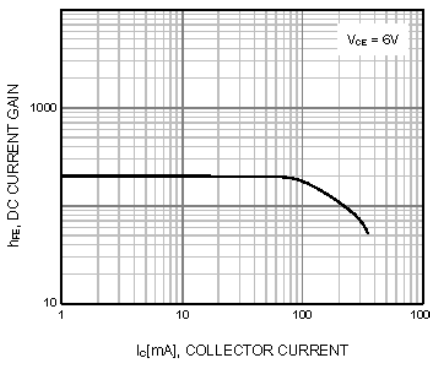




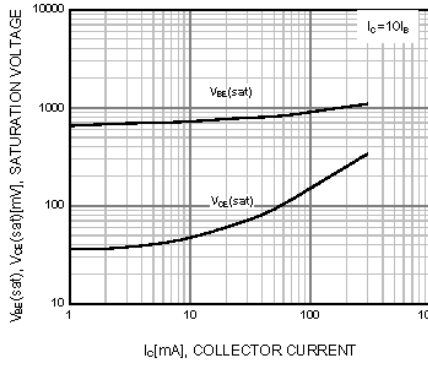
Static Characteristic



Transfer Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

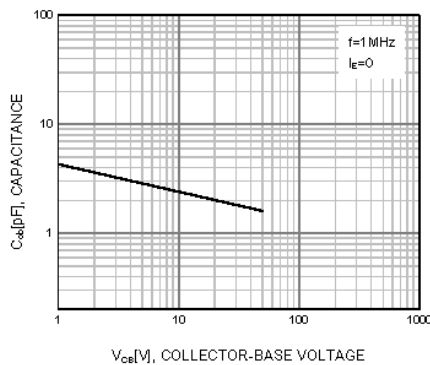


Figure 5. Output Capacitance

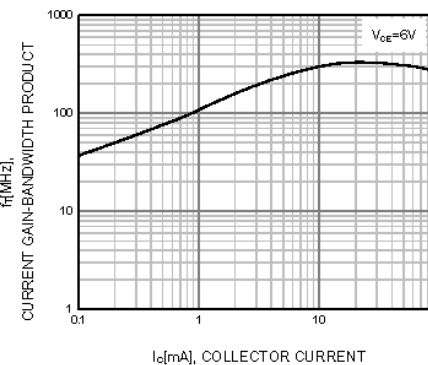


Figure 6. Current Gain Bandwidth Product

